CPH6445

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N-Channel Power MOSFET 60V, 3.5A, 117m Ω , Single CPH6

Features

- · 4V drive
- · Low ON-resistance
- · Protection diode in

Specifications

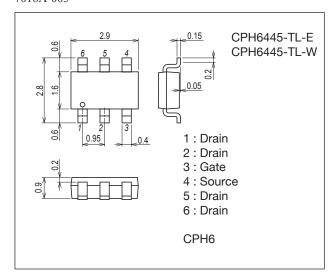
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		60	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		3.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	14	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Package Dimensions

unit : mm (typ) 7018A-003



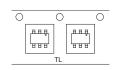
Product & Package Information

• Package : CPH6

• JEITA, JEDEC : SC-74, SOT-26, SOT-457

• Minimum Packing Quantity : 3,000 pcs./reel

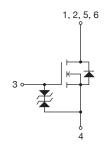
Packing Type: TL



Marking



Electrical Connection



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

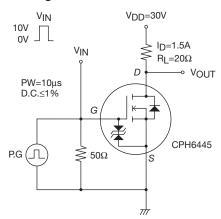
CPH6445

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Parameter		Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	60			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =60V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA 1.2			2.6	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1.5A 1.2		2.0		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=1.5A, VGS=10V		92	117	mΩ
	R _{DS} (on)2	I _D =0.7A, V _{GS} =4.5V		120	168	mΩ
	R _{DS} (on)3	I _D =0.7A, V _G S=4V		132	185	mΩ
Input Capacitance	Ciss			310		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		40		pF
Reverse Transfer Capacitance	Crss			25		pF
Turn-ON Delay Time	t _d (on)			6.0		ns
Rise Time	t _r	Construction of Total Circuit		5.5		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		27		ns
Fall Time	tf			13		ns
Total Gate Charge	Qg			6.8		nC
Gate-to-Source Charge	Qgs	V _{DS} =30V, V _{GS} =10V, I _D =3.5A		1.1		nC
Gate-to-Drain "Miller" Charge	Qgd	1		1.4		nC
Diode Forward Voltage	V _{SD}	I _S =3.5A, V _{GS} =0V		0.85	1.2	V

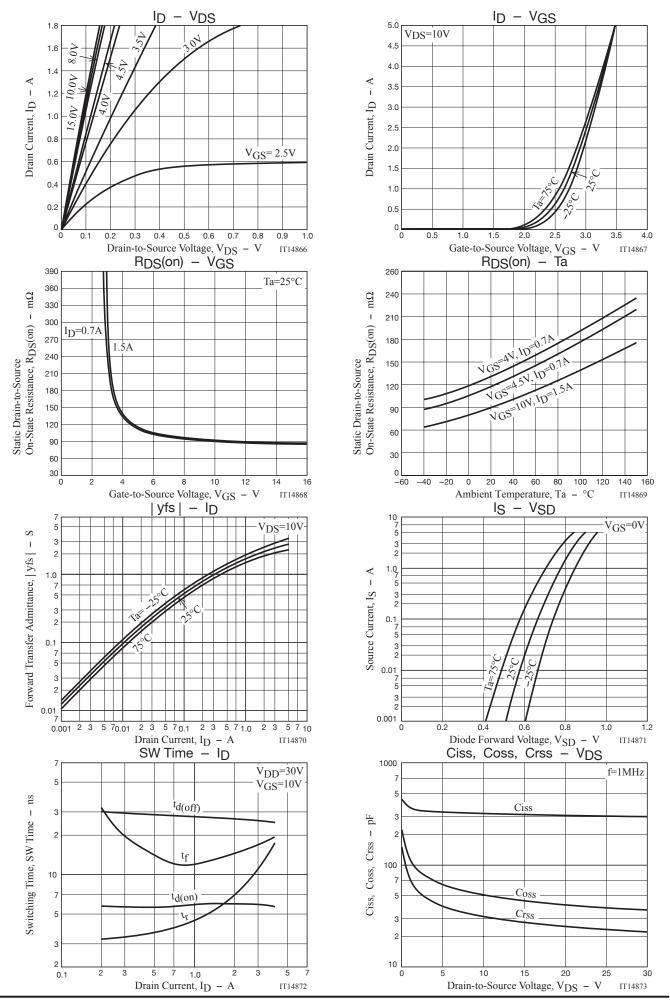
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

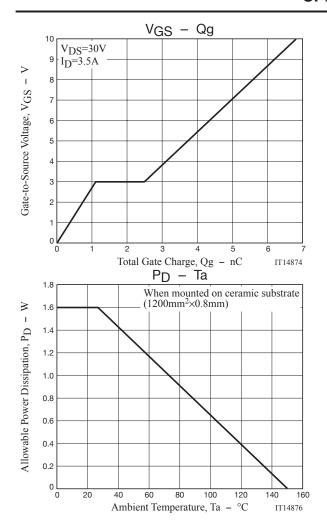
Switching Time Test Circuit

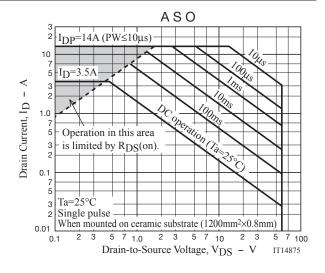


Ordering Information

Device	Package	Shipping	memo	
CPH6445-TL-E	CPH6	2 000000 (real	Pb-Free	
CPH6445-TL-W	CPH6	3,000pcs./reel	Pb-Free and Halogen Free	



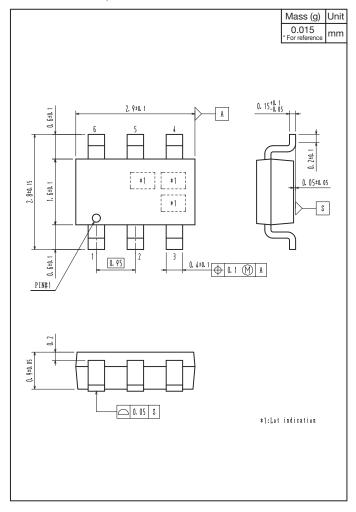


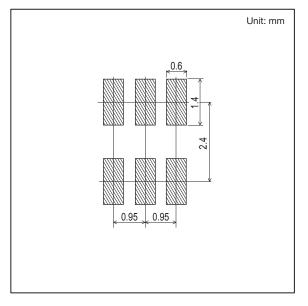


Outline Drawing

CPH6445-TL-E, CPH6445-TL-W

Land Pattern Example





Note on usage: Since the CPH6445 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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